

PHPT61003PY

100 V, 3A PNP high power bipolar transistor

13 January 2014

Product data sheet

1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT61003NY

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management
- Loadswitch
- Linear mode voltage regulator
- Backlighting applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-100	V
I _C	collector current		-	-	-3	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse	-	-	-8	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -200 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	110	180	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	Е	emitter		В—
3	Е	emitter	[d	'*_
4	В	base	<u>o o o o</u>	sym132
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PHPT61003PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61003PY	1003PAB

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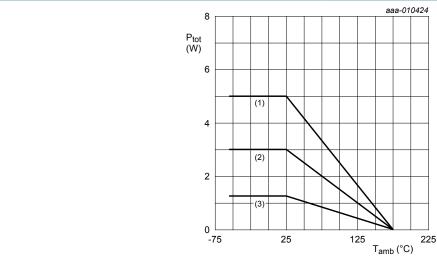
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-100	V
V_{CEO}	collector-emitter voltage	open base		-	-100	V
V _{EBO}	emitter-base voltage	open collector		-	-8	V
I _C	collector current			-	-3	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	-8	Α
I _B	base current			-	-0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
T_j	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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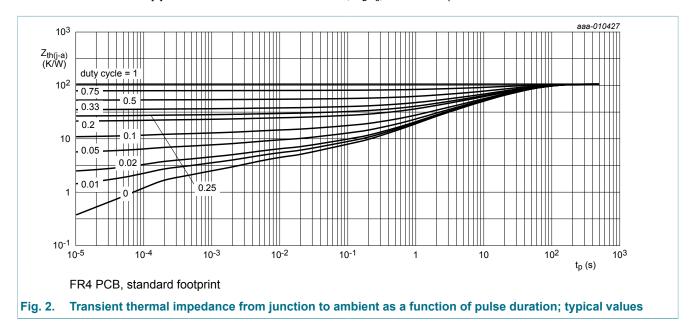
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9. Thermal characteristics

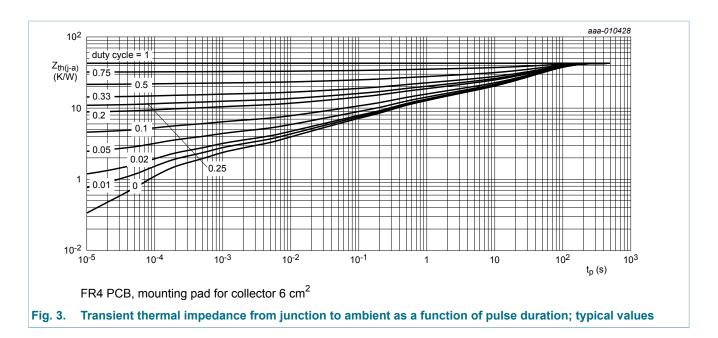
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ang a)	thermal resistance		[1]	-	-	115	K/W
	from junction to		[2]	-	-	50	K/W
	ambient		[3]	-	-	30	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.



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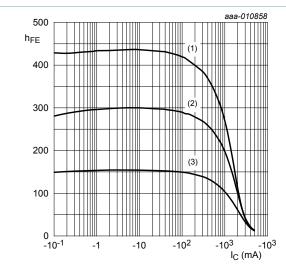
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	$V_{CE} = -80 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -8 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V}; I_{C} = -500 \text{ mA};$ $T_{amb} = 25 \text{ °C}$	150	220	-	
		V_{CE} = -10 V; I_{C} = -1 A; t_{p} ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C; pulsed	80	210	-	
		V_{CE} = -10 V; I_{C} = -2 A; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C; pulsed	20	100	-	
		V_{CE} = -10 V; I_{C} = -3 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	10	40	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -500 mA; I_B = -50 mA; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-70	-110	mV
		I_{C} = -2 A; I_{B} = -200 mA; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-220	-360	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	110	180	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -1 A; I_B = -50 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	-0.91	-1	V
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-1.02	-1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -100 mA; T_{amb} = 25 °C	-	-0.68	-0.9	V
t _d	delay time	V_{CC} = -12.5 V; I_{C} = -1 A; I_{Bon} = -50 mA;	-	20	-	ns
t _r	rise time	I_{Boff} = 50 mA; T_{amb} = 25 °C	-	180	-	ns
t _{on}	turn-on time		-	200	-	ns
t _s	storage time		-	350	-	ns
t _f	fall time		-	220	-	ns
t _{off}	turn-off time		-	570	-	ns
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	-	125	-	MHz

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$	-	30	-	pF
		f = 1 MHz; T _{amb} = 25 °C				



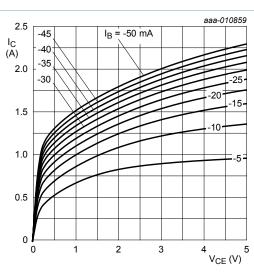
 $V_{CE} = -10 \text{ V}$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

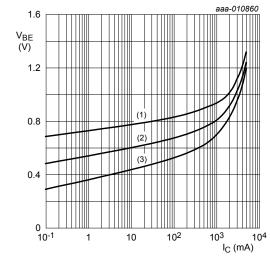
(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 4. DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



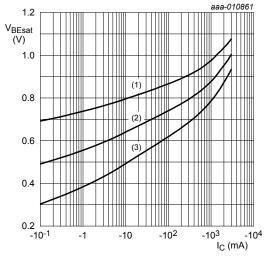
 $V_{CE} = -2 V$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 20$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb}$$
 = 25 °C

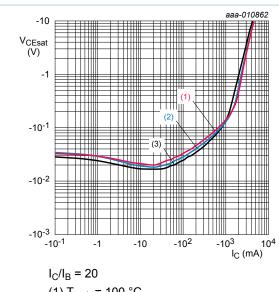
(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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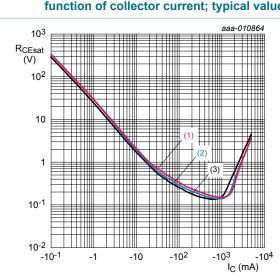


(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



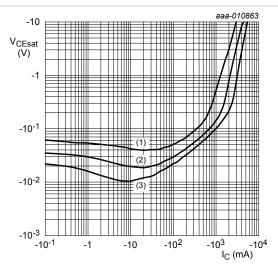
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



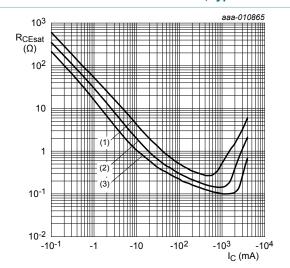
$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 50$$

(2)
$$I_C/I_B = 20$$

(3)
$$I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 50$$

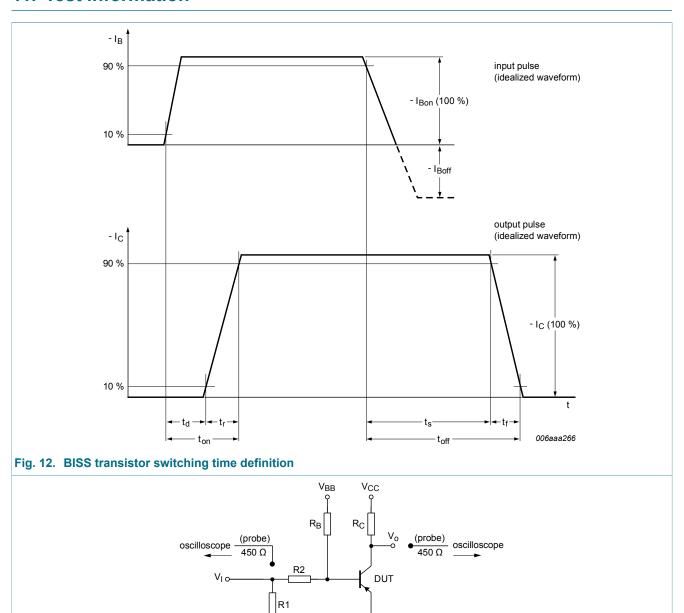
(2)
$$I_C/I_B = 20$$

(3)
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information



11.1 Quality information

Fig. 13. Test circuit for switching times

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

mgd624

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12. Package outline

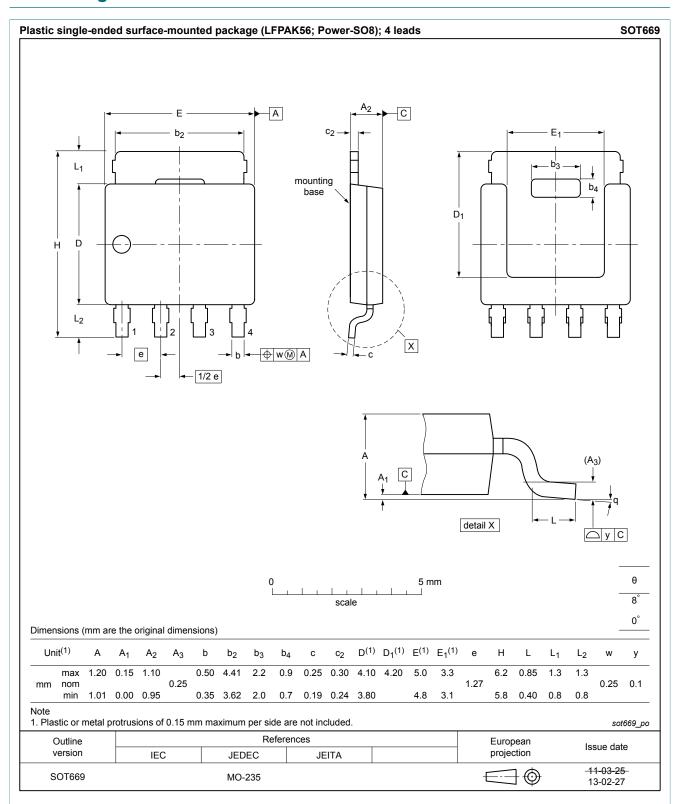


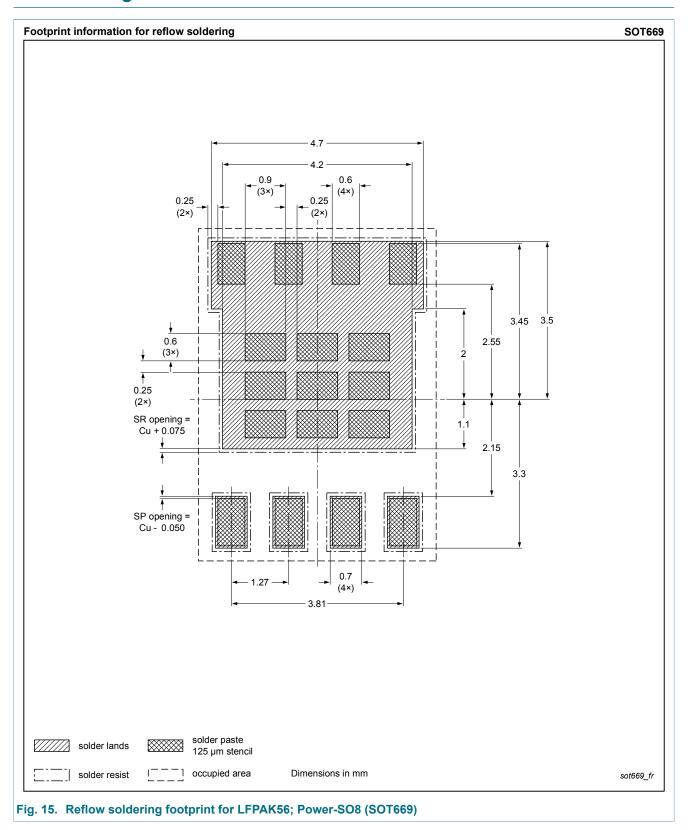
Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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13. Soldering



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14. Revision history

Table 8. **Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61003PY v.1	20140113	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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